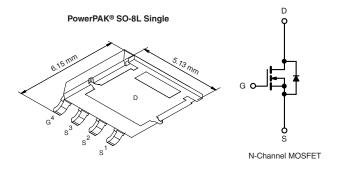


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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	60
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.017
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.020
I _D (A)	24
Configuration	Single



FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % Rq and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ464EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	5 (T _C = 25 °C, unles	s otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	60	V		
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Currenta	T _C = 25 °C	1	32		
Continuous Drain Current	T _C = 125 °C	I _D	18		
Continuous Source Current (Diode Conduction	I _S	41	Α		
Pulsed Drain Current ^b		I _{DM}	130		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	25		
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	31	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	45	W	
	T _C = 125 °C	P_{D}	15	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	70	°C/W
Junction-to-Case (Drain)		R_{thJC}	3.3	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				L		L	ı
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 7.1 A	-	0.0140	0.0170	
Dunin Course On Otata Basistanas		V _{GS} = 4.5 V	I _D = 6.5 A	-	0.0165	0.0200	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 7.1 A, T _J = 125 °C	-	-	0.0310	Ω
		V _{GS} = 10 V	I _D = 7.1 A, T _J = 175 °C	-	-	0.0410	
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 7.1 A	-	60	-	S
Dynamic ^b		<u> </u>					
Input Capacitance	C _{iss}			-	1670	2086	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	145	181	pF
Reverse Transfer Capacitance	C _{rss}	7		-	59	74	
Total Gate Charge ^c	Qg			-	29	44	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 6 \text{ A}$	-	4.9	-	nC
Gate-Drain Charge ^c	Q _{gd}	7		-	4.9	-	
Gate Resistance	R _g		f = 1 MHz	0.45	0.91	2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	7.7	11.5	
Rise Time ^c	t _r	V _{DD} :	= 30 V, $R_1 = 30 \Omega$	-	8.9	13.4	
Turn-Off Delay Time ^c	t _{d(off)}		$V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$	-	25.4	38	ns
Fall Time ^c	t _f	7		-	8.8	13.2	
Source-Drain Diode Ratings and Char	acteristics ^b	•					
Pulsed Current ^a	I _{SM}			-	-	96	Α
Forward Voltage	V _{SD}	I _F :	= 4.8 A, V _{GS} = 0	-	0.8	1.2	V

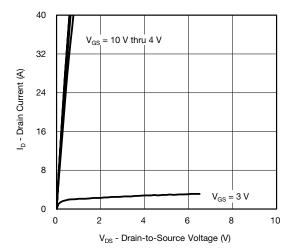
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

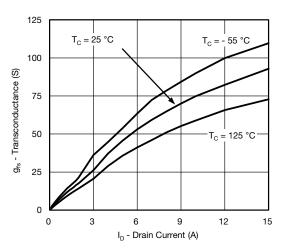
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



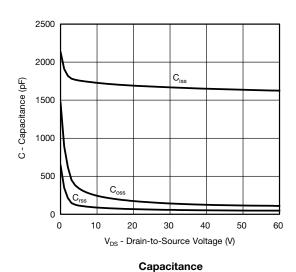
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics

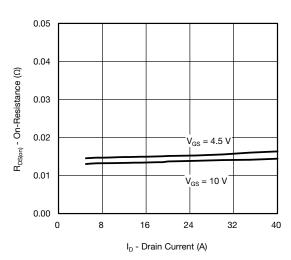


Transconductance

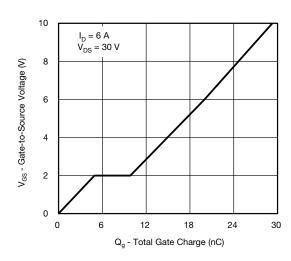


32 (4) 32 T_C = 25 °C T_C = 125 °C T_C = -55 °C V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

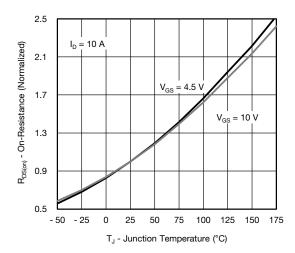


On-Resistance vs. Drain Current

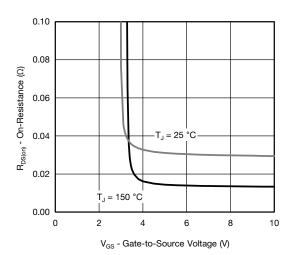




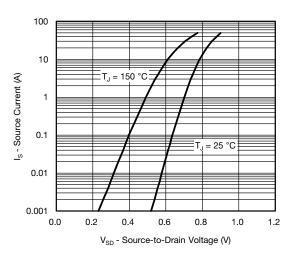
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



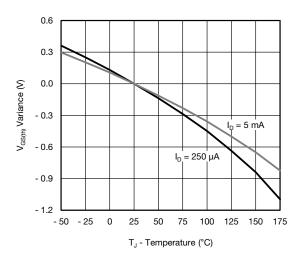
On-Resistance vs. Junction Temperature



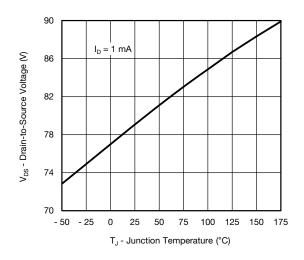
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



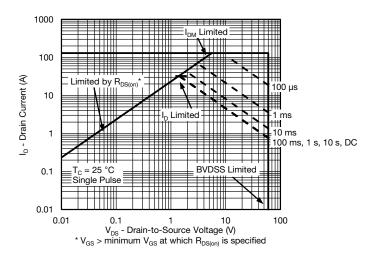
Threshold Voltage



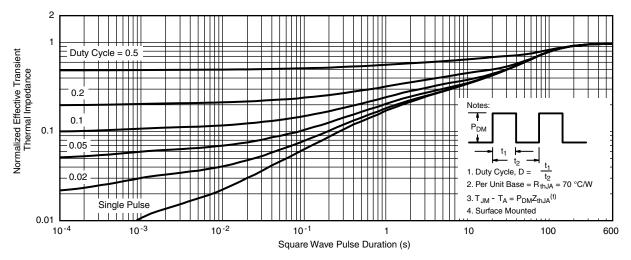
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



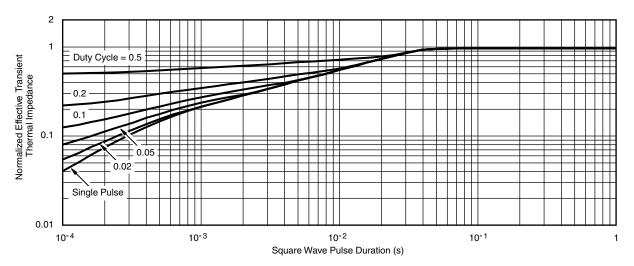
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

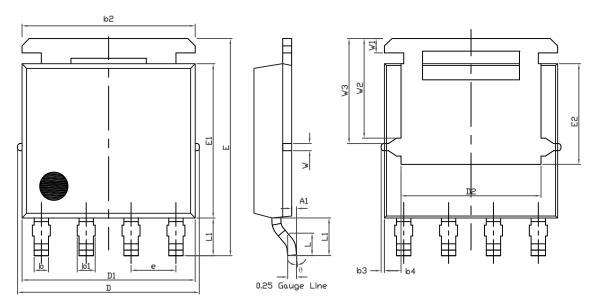
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

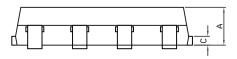
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65397.

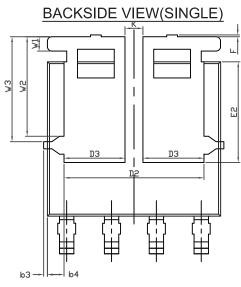


PowerPAK® SO-8L Case Outline 2



TOPSIDE VIEW





BACKSIDE VIEW(DUAL)



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	NOM. MAX. MIN. NOM.					
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23		0.009				
W1		0.41		0.016				
W2	2.82		0.111					
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

ECN: S19-0643-Rev. B, 05-Aug-2019

DWG: 6044

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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